

## HIGH VOLTAGE FAST -SWITCHING NPN POWER TRANSISTOR

### DESCRIPTION

This Device is designed for high voltage, High speed switching characteristics required such as compact electronic energy saving lamps , electronic ballast and mobile phone chargers power Switch circuit, is the core component of such electronic products.


**TO-220AB PACKAGE**

### FEATURES

- Very High Switching Speed
- High Voltage Capability
- Wide Reverse Bias SOA
- Built-in freewheeling diode

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Test Conditions	Value	Unit
V <sub>CES</sub>	Collector -Emitter Voltage	V <sub>BE</sub> =0	700	V
V <sub>CEO</sub>	Collector -Emitter voltage	I <sub>B</sub> =0	400	V
V <sub>EBO</sub>	Emitter-Bade Voltage	I <sub>C</sub> =0	9.0	V
I <sub>C</sub>	Collector Current		4.0	A
I <sub>CP</sub>	Collector pulse Current		8.0	A
I <sub>B</sub>	Base Current		2.0	
I <sub>BM</sub>	Base Peak Current	t <sub>p</sub> = 5ms	4.0	
P <sub>C</sub>	Total dissipation at T <sub>c</sub> =25 °C		75	W
T <sub>J</sub>	Operation Junction Temperature		150	°C
T <sub>STG</sub>	Storage Temperature		-40~150	°C

### ELECTRICAL CHARACTERISTICS(T<sub>c</sub>=25°C UNLESS OTHERWISE NOTED)

Symbol	Parameter	Test Conditions	Value			Units
			Min	Typ	Max	
I <sub>CEV</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5V )	V <sub>CE</sub> = 700V V <sub>CE</sub> = 700V ,T <sub>c</sub> = 100 °C	-	-	1.0 5.0	mA
V <sub>CEO(sus)</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA,I <sub>B</sub> =0	400	-	-	V
V <sub>CE(sat)</sub>	Collector -Emitter Saturation Voltage	I <sub>C</sub> =1.0A, I <sub>B</sub> = 0.2A I <sub>C</sub> = 2.0A, I <sub>B</sub> = 0.5A I <sub>C</sub> = 4.0A, I <sub>B</sub> = 1.0A	-	-	0.5 0.6 1.0	V
V <sub>BE(sat)</sub>	Base -Emitter Saturation Voltage	I <sub>C</sub> =1.0A, I <sub>B</sub> = 0.2A I <sub>C</sub> = 2.0A, I <sub>B</sub> = 0.5A	-	-	1.2 1.6	V
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 1.0A, V <sub>CE</sub> = 5V I <sub>C</sub> = 2.0A, V <sub>CE</sub> = 5V	10 10	-	40 30	
f <sub>T</sub>	Characteristic frequency	I <sub>C</sub> =0.5A ,V <sub>CE</sub> =10V	4	-	-	MHz
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> =2A	-	-	2.5	V

**Note:** Pulse Test : Pulse width 300,Duty cycle 2%

**THERMAL CHARACTERISTICS**

Symbol	Parameter	Value	Unit
$R_{thjc}$	Thermal resistance, Junction to case	1.67	°C/W
$R_{thja}$	Thermal resistance, Junction to ambient	62.5	

**TO-220 PACKAGE**

Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	3.56	4.83	0.140	0.190
A1	2.03	2.92	0.080	0.115
b	0.38	1.02	0.015	0.040
b1	1.14	1.78	0.045	0.070
C	0.51	1.40	0.020	0.055
C1	0.36	0.61	0.014	0.024
D	9.65	10.67	0.380	0.420
E	14.22	16.51	0.560	0.650
e	2.54BSC		0.10BSC	
F	2.54	3.05	0.100	0.120
G	3.53	3.90	0.139	0.154
H	12.70	14.73	0.500	0.580
L	5.84	6.86	0.230	0.270
L1	-	6.35	-	0.250

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